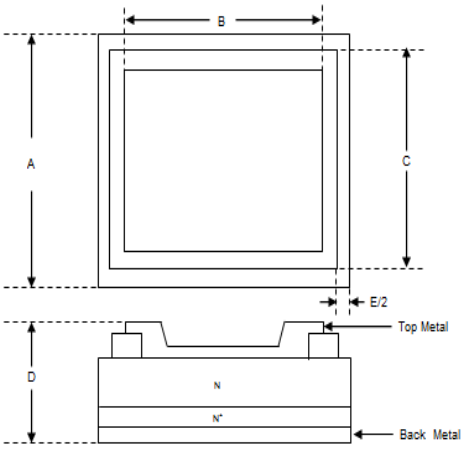
TSB82T100S(A)S-255C

10A/100V(1), low VF Schottky barrier diode with trench MOS structure

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2082 μm	82 mil
	Top Metal Pad Size (B)	1950μm	77mil
	Chip Size (C)	2002μm	79mil
	Wafer Thickness (D)	255 μm	9.5 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	Al/Ag	
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 ±3)	

Electrical Characteristics (T_J=25℃, unless otherwise specified)(2)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	105	109	-	V	I_R =100μA
V_F	Instantaneous Forward Voltage	-	0.53	0.59	V	I_F =5A(3)
		-	0.65	0.70	V	I_F =10A(3)
I_R	Reverse Leakage Current	-	15	50		V_R =105V
T_J, T_{STG}	Operating and Storage Temperature	-40 to 150 Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assume the dies are assembled in SMC packages. Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) ;